

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





1. General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	-	140	A
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	16	A
Static chara	cteristics		· ·			
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G-;	-	-	10	mA
		T _j = 25 °C; <u>Fig. 7</u>				

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	Т2	main terminal 2		sym051
3	G	gate		
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3.Ordering information

Type number	Package					
	Name	Description	Version			
BTA316-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BTA316-600E/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BTA316-600E	
BTA316-600E/DG	BTA316-600EDG

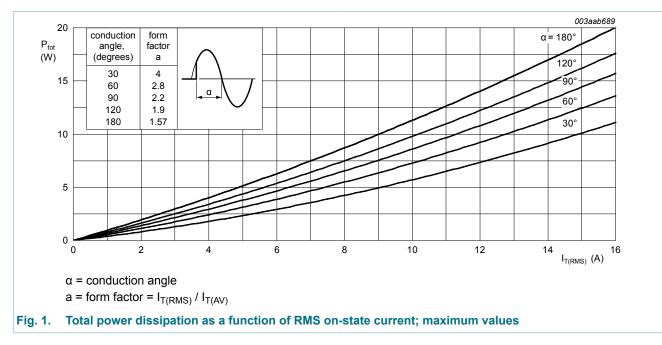
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8. Limiting values

Table 5.Limiting values

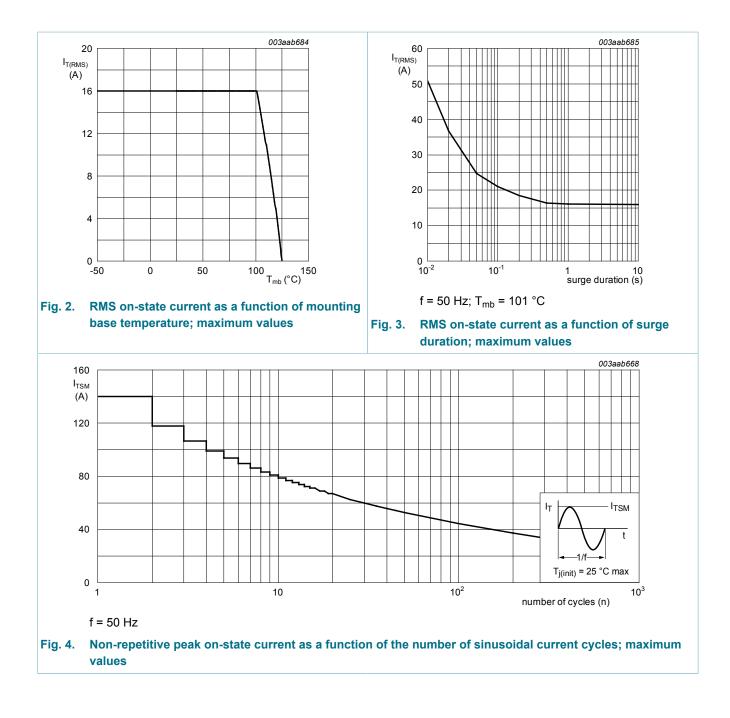
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	16	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{Fig. 4}; \text{Fig. 5}$	-	140	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	150	A
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	98	A ² s
dI _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



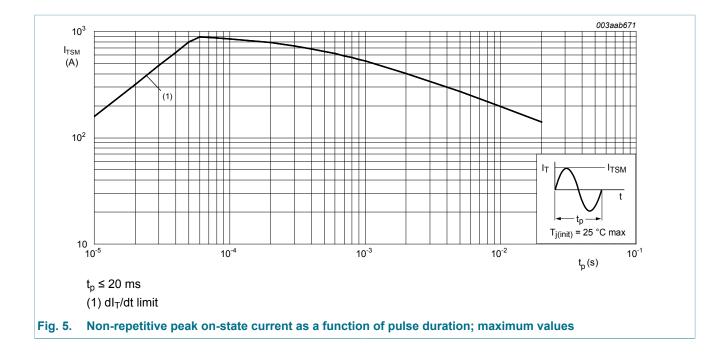
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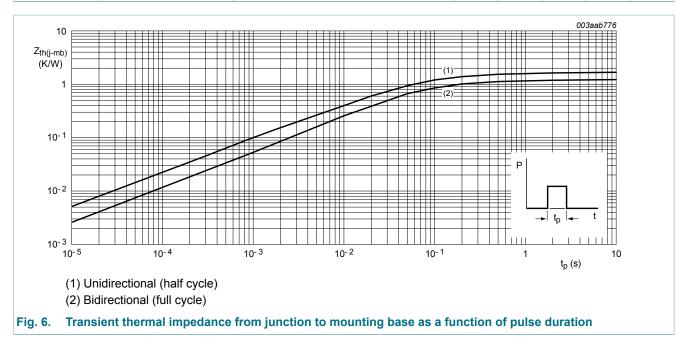
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9. Thermal characteristics

Table 6. 1	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 6	-	-	1.2	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · · · ·				
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	-	10	mA
		V_D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
IL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	25	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
ID	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cł	naracteristics	· · · · ·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	60	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 16 A; dV _{com} /dt = 20 V/µs; (snubberless condition); gate open circuit	5	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; dV _{com} /dt = 10 V/µs; gate open circuit	8	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; dV _{com} /dt = 1 V/µs; gate open circuit	12	-	-	A/ms

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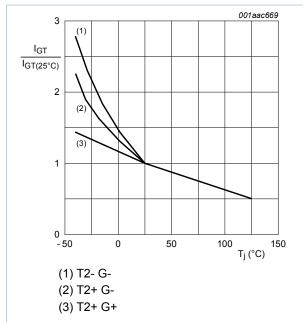


Fig. 7. Normalized gate trigger current as a function of junction temperature

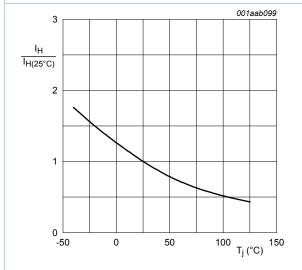
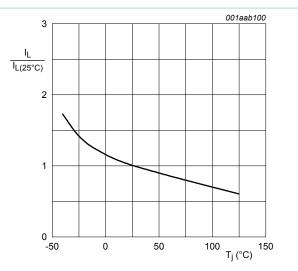
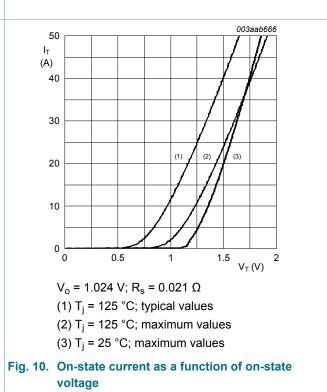


Fig. 9. Normalized holding current as a function of junction temperature



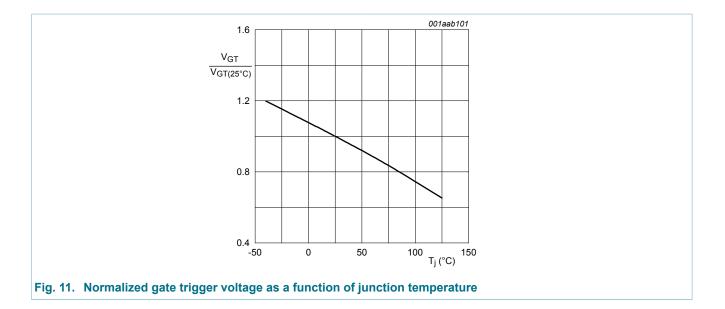




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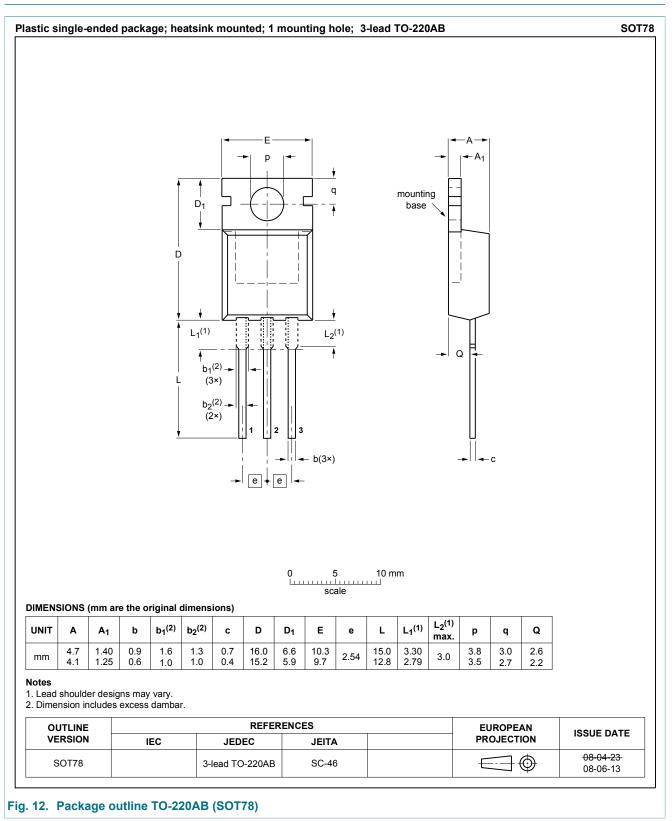


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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	
9	Thermal characteristics	6
10	Characteristics	7
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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